

NTE570 Silicon Controlled Avalanche Diode

Absolute Maximum Ratings:

Peak Reverse Voltage, V_{RM} 130V
 Allowable Avalanche Current (Square Wave Single Pulse 100 μ s), I_{ZSM} 1.0A
 Operating Junction Temperature Range, T_J -40° to +150°C
 Storage temperature Range, T_{stg} -40° to +150°C

Electrical Characteristics: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Avalanche Voltage	V_Z	$I_Z = 1\text{mA}$ Instantaneous	135	—	180	V
Reverse Current	I_R	$V_R = 130\text{V}$	—	—	10	μA
Reverse Current (High Temperature)	$I_{R(H)}$	$V_R = 130\text{V}$, $T_A = +100^\circ\text{C}$	—	—	50	μA
Temperature Dependency of V_Z	J	$I_Z = 1\text{mA}$	—	0.15	—	V/ $^\circ\text{C}$

